

DR. N. CHANDRA

KHENTAWAS, FARRUKHNAGAR, GURGAON, HR

Department: ECE

Academic Session: 2017-18 (Jan-June 2018)

Lesson Plan for the Semester started w.e.f 08.01.2018

Subject with code: VLSI DESIGN (EE-306-F)

Name of Faculty with designation : Krishanu Kundu, Asst. Prof

| Month | Date & Day | Sem-Class | Unit | Topic/Chapter covered | Academic activity | Test / assignment |
|---------|-------------------------|------------|------|---|-------------------|------------------------------|
| January | 10.01.2018 Wednesday | VI-ECE/EEE | 1 | Introduction to MOSFETs -Description of MOSFETs -Operation of Enhancement mode & Depletion mode MOSFET -Description & structure of n-MOS & p-MOS -Description & structure of CMOS | | Assignment of 02 Ques. given |
| January | 11.01.2018 Thursday | VI-ECE/EEE | 1 | Equivalent circuit of n-MOS ,p-MOS & CMOS -Threshold voltages for n-MOS and p-MOS Drain current characteristics of E-type & D-type n-MOSFET -Identification of regions of operation of the MOSFETs -Conductance characteristics of E-type & D-type n-MOSFET | | Assignment of 02 Ques. given |
| January | 17.01.2018 Wednesday | VI-ECE/EEE | 1 | structure of Enhancement mode n-MOSFET -Polarities of voltages applied to Gate, Drain, Source & Substrate. Formation of channel in enhancement mode MOSFET Derivation of mathematical expression for Drain current I_{DS} for n-MOS and p-MOS | | Assignment of 02 Ques. given |
| January | 18.01.2018 Thursday | VI-ECE/EEE | 1 | Diagram of structure of n-MOS & p-MOS & voltage polarities. Definition of Threshold voltage & substrate bias. Work function difference between gate and Si Fermi level potential between inverted surface and bulk Si Expression for Threshold voltage Meaning & Expression of Body effect | | Assignment of 02 Ques. given |
| January | 24.01.2018 Wednesday | VI-ECE/EEE | 1 | Subthreshold region -Channel length Modulation -Mobility variation -Fowler-Nordheim Tunnelling -Drain Punchthrough -Impact ionization-Hot electrons | | Assignment of 02 Ques. given |

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| January | 25.01.2018 Thursday | VI-ECE/EEE | 1 | MOS device transconductance - figure of merit - Small signal equivalent model AC characteristics - Output conductance - Channel resistance | | Assignment of 02 Ques. given |
| January | 23.01.2018 Tuesday | VI-ECE/EEE | 1 | Different configurations of MOS switches and MOS loads -Output characteristics for different ratios of (W/L)driver/ (W/L) | | Assignment of 02 Ques. given |
| January | 1.02.2018 Thursday | VI-ECE/EEE | 1 | Principle & Working of Latch –up circuit Latch-up circuit Model BiCMOS inverter Circuit V-I characteristics of TTL | | Test |
| January | 7.02.2018 Wednesday | VI-ECE/EEE | 2 | Derivation of n-MOS inverter transfer characteristic & threshold voltage of inverter. -Effect of variation of (Z_{pu} / Z_{pd}) on the transfer characteristic | | Assignment of 02 Ques. given |
| January | 8.02.2018 Thursday | VI-ECE/EEE | 2 | Basic principle of CMOS Working of CMOS DC characteristics of CMOS β_n / β_p ratio Noise Margin CMOS Inverter as an Amplifier | | Assignment of 02 Ques. given |
| February | 21.02.2018 Wednesday | VI-ECE/EEE | 2 | Basic configuration of MOS switch with load resistance RL -Configuration of MOS switch and n-MOS depletion mode transistor pull up -Configuration of MOS switch and n-MOS enhancement mode transistor pull up | | Assignment of 02 Ques. given |
| February | 22.02.2018 Thursday | VI-ECE/EEE | 2 | MOS AS PASS TRANSISTOR & DETERMINATION OF PULL UP/PULL DOWN RATIO FOR n-MOS INVERTER DRIVEN BY ANOTHER n-MOS INVERTER /PASS TRANSISTOR | | Assignment of 02 Ques. given |
| February | 28.02.2018 Wednesday | VI-ECE/EEE | 2 | A generic static load inverter -The Pseudo –n MOS inverters -Saturated load inverters using n MOS transistor load -The Cascode inverter -TTL interface inverter | | Assignment of 02 Ques. given |

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| March | 7.03.2018 Wednesday | VI-ECE/EEE | 2 | A simple inverter (basic gates) transistor model -The rule for designing STICK DIAGRAM for pMOS and nMOS transistors -Substitution of stick bar in place of transistors | | Assignment of 02 Ques. given |
| March | 8.03.2018 Thursday | VI-ECE/EEE | 2 | Discussion on Lambda based rules An inverter layout -The distance gap within different construction material used for transistor model. -Design Rule Check -Channel length parameter -Latest technology trends | | Assignment of 02 Ques. given |
| March | 14.03.2018 Wednesday | VI-ECE/EEE | 2 | Super Buffers classification, BiCMOS Features - Gates design BiCMOS -Steering Logic through multiplexer -Few examples implementation by Steering logic | | Test |
| March | 15.03.2018 Thursday | VI-ECE/EEE | 3 | Combinational circuit Boolean expression minimization - Expression realization with the pMOS - Expression realization with the nMOS - Realization of digital circuits using cMOS Tristate Inverter | | Assignment of 02 Ques. given |
| March | 28.03.2018 Wednesday | VI-ECE/EEE | 3 | V-I CMOS Logic Structures Clocking Strategies Estimation of R, Resistance of Nonrectangular Regions Contact and Via Resistance Refresh loop ,Parallel load mode, Shift right mode Shift left mode, Parallel out put, Isolation of inverters | | Assignment of 02 Ques. given |
| March | 4.04.2018 Wednesday | VI-ECE/EEE | 3 | Analytic Delay Models of -Rise Time, tr, -Fall Time, tf, -Delay Time, td Empirical Delay Models | | Test |
| April | 5.04.2018 Thursday | VI-ECE/EEE | 4 | Introduction to CAD tools, Use of CAD tools Introduction to VHDL: Structural Modeling Data Flow Modeling , Behavioral Modeling OBJECTS, CLASSES, DATA TYPES, OPERATORS | | Assignment of 02 Ques. given |
| April | 11.04.2018 Wednesday | VI-ECE/EEE | 4 | Libraries and Packages , Overloading Programmable Logic Devices. • Programmable Array Logic • Programmable Logic Array • FPGA • ROM | | Assignment of 02 Ques. given |

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| April | 12.04.2018 Thursday | VI-ECE/EEE | 4 | ROM(Read Only Memory) as PLD PLA(Programmable Logic Array) and PAL(Programmable Array Logic) FPGA(Field Programmable Gate Array) CPLD's(Complex Programmable Logic Devices) | | Test |